Rongdun Hong

List of Publications by Year in descending order

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1684188 1588992 16 76 5 8 citations g-index h-index papers 16 16 16 94 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Solution growth of crystalline ZnO thin film and its photodetector application. Physica E: Low-Dimensional Systems and Nanostructures, 2018, 104, 16-21.	2.7	16
2	High performance silicon carbide avalancheâ€pâ€iâ€n ultraviolet photodiode with dual operation models. Electronics Letters, 2016, 52, 1474-1476.	1.0	11
3	Enhancing the photoelectrical performance of graphene/4H-SiC/graphene detector by tuning a Schottky barrier by bias. Applied Physics Letters, 2020, 117, .	3.3	11
4	Effect of epitaxial layer's thickness on spectral response of 4Hâ€SiC pâ€iâ€n ultraviolet photodiodes. Electronics Letters, 2019, 55, 216-218.	1.0	8
5	Local Avalanche Effect of 4H-SiC p-i-n Ultraviolet Photodiodes With Periodic Micro-Hole Arrays. IEEE Electron Device Letters, 2022, 43, 64-67.	3.9	7
6	Characteristics of graphene/4H-SiC/graphene photodetector based on hydrogenated multilayer-graphene electrode. Journal of Nanophotonics, 2019, 13, 1.	1.0	4
7	4H-SiC Nano-Pillar Avalanche Photodiode With Illumination-Dependent Characteristics. IEEE Photonics Technology Letters, 2011, 23, 816-818.	2.5	3
8	Nanoscale avalanche photodiode with self-quenching and ultrahigh ultraviolet/visible rejection ratio. Optics Letters, 2012, 37, 3651.	3.3	3
9	Effect of interfacial dipole on heterogeneous ice nucleation. Journal of Physics Condensed Matter, 2021, 33, 375001.	1.8	3
10	Effect of rapid thermal annealing on Zn/ZnO layers. Journal of Materials Science: Materials in Electronics, 2013, 24, 4075-4079.	2.2	2
11	TiNbO ₂ -Based Photodetectors With Low Dark Current and High UV-to-Visible Rejection Ratio. IEEE Photonics Technology Letters, 2016, 28, 837-840.	2.5	2
12	Raman Spectroscopy of Multi-Layer Graphene epitaxially Grown on 4H-SiC by Joule Heat Decomposition. Nanoscale Research Letters, 2018, 13, 197.	5.7	2
13	Charge layer optimized 4H-SiC SACM avalanche photodiode with low breakdown voltage and high gain. Japanese Journal of Applied Physics, 2019, 58, 100913.	1.5	2
14	MgxZn1â^'xO Prepared by the Sol–Gel Method and Its Application for Ultraviolet Photodetectors. Journal of Electronic Materials, 2020, 49, 4518-4523.	2.2	2
15	Ellipsometry, FTIR, Raman and X-Ray Spectroscopy Analysis of PECVD a-Si1-xCx:H Film. Spectroscopy Letters, 2010, 43, 298-305.	1.0	0
16	Optimization of 4H-SiC separated-absorption-charge-multiplication (SACM) avalanche photodiode with low avalanche breakdown voltage. , 2011, , .		0